

Amendment to the Specification:

On page 1, line 1, replace the title with the following title:

--STRUCTURES WITH PLANAR STRAINED LAYERS--

On page 1, after "Related Applications" please replace lines 4-5 with the following paragraph:

--This application is a divisional of application Serial No. 10/211,126, filed on August 2, 2002, which claims the benefit of U.S. Provisional Application No. 60/310,346, filed August 6, 2001, now expired, the entire disclosures of which are incorporated by reference herein.--

On page 16, amend the Abstract as follows:

A structure ~~and a method for forming the structure, the method including forming~~ a compressively strained semiconductor layer, the compressively strained layer having a strain greater than or equal to 0.25%. A tensilely strained semiconductor layer ~~[is]~~may be formed over the compressively strained layer. The compressively strained layer is substantially planar, having a surface roughness characterized in (i) having an average wavelength greater than an average wavelength of a carrier in the compressively strained layer and/or (ii) having an average height less than 10 nm.